

## NCE N-Channel Super Trench II Power MOSFET

### Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

### General Features

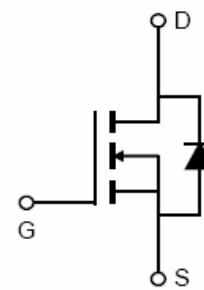
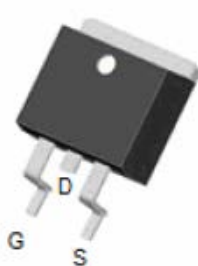
- $V_{DS} = 85V, I_D = 95A$   
 $R_{DS(ON)} = 5.4m\Omega$ , typical (TO-220) @  $V_{GS} = 10V$   
 $R_{DS(ON)} = 5.2m\Omega$ , typical (TO-263) @  $V_{GS} = 10V$
- Excellent gate charge x  $R_{DS(on)}$  product(FOM)
- Very low on-resistance  $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

**100% UIS TESTED!**  
**100%  $\Delta V_{ds}$  TESTED!**

TO-220



TO-263



Schematic Diagram

### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HMS85N95	HMS85N95	TO-220	-	-	-
HMS85N95D	HMS85N95D	TO-263	-	-	-

### Absolute Maximum Ratings ( $T_C = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	85	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	95	A
Drain Current-Continuous( $T_C = 100^\circ C$ )	$I_D(100^\circ C)$	70	A
Pulsed Drain Current	$I_{DM}$	380	A
Maximum Power Dissipation	$P_D$	125	W
Derating factor		0.83	W/ $^\circ C$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	460	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ C$

**Thermal Characteristic**

Thermal Resistance,Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	1.2	$^{\circ}C/W$
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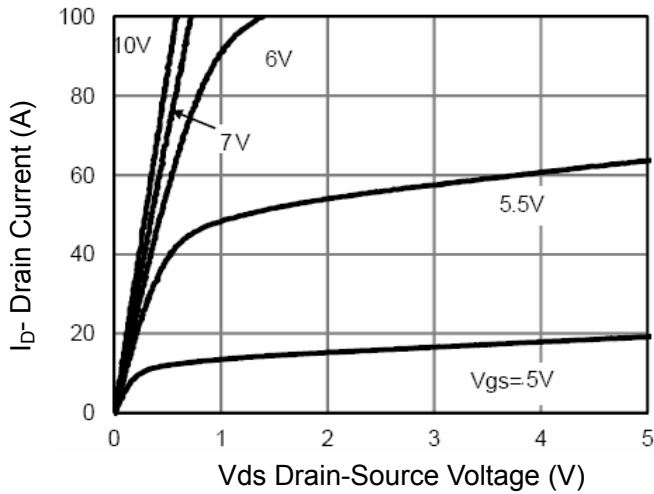
**Electrical Characteristics ( $T_C=25^{\circ}C$  unless otherwise noted)**

Parameter	Symbol	Condition	Min	Typ	Max	Unit	
<b>Off Characteristics</b>							
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V, I_D=250\mu A$	85		-	V	
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=85V, V_{GS}=0V$	-	-	1	$\mu A$	
Gate-Body Leakage Current	$I_{GSS}$	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	$\pm 100$	nA	
<b>On Characteristics</b> <sup>(Note 3)</sup>							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0	3.0	4.0	V	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=45A$	TO-220	-	5.4	5.8	m $\Omega$
			TO-263		5.2	5.8	m $\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS}=5V, I_D=45A$		60	-	S	
<b>Dynamic Characteristics</b> <sup>(Note 4)</sup>							
Input Capacitance	$C_{iss}$	$V_{DS}=40V, V_{GS}=0V,$ $F=1.0MHz$	-	3550	-	PF	
Output Capacitance	$C_{oss}$		-	540	-	PF	
Reverse Transfer Capacitance	$C_{rss}$		-	22	-	PF	
<b>Switching Characteristics</b> <sup>(Note 4)</sup>							
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=40V, I_D=45A$ $V_{GS}=10V, R_G=1.6\Omega$	-	14.5	-	nS	
Turn-on Rise Time	$t_r$		-	12	-	nS	
Turn-Off Delay Time	$t_{d(off)}$		-	35	-	nS	
Turn-Off Fall Time	$t_f$		-	13	-	nS	
Total Gate Charge	$Q_g$	$V_{DS}=40V, I_D=45A,$ $V_{GS}=10V$	-	67	-	nC	
Gate-Source Charge	$Q_{gs}$		-	20		nC	
Gate-Drain Charge	$Q_{gd}$		-	20		nC	
<b>Drain-Source Diode Characteristics</b>							
Diode Forward Voltage <sup>(Note 3)</sup>	$V_{SD}$	$V_{GS}=0V, I_S=45A$	-		1.2	V	
Diode Forward Current <sup>(Note 2)</sup>	$I_S$		-	-	95	A	
Reverse Recovery Time	$t_{rr}$	$T_J = 25^{\circ}C, I_F = I_S$ $di/dt = 100A/\mu s$ <sup>(Note 3)</sup>	-	66	-	nS	
Reverse Recovery Charge	$Q_{rr}$		-	140	-	nC	

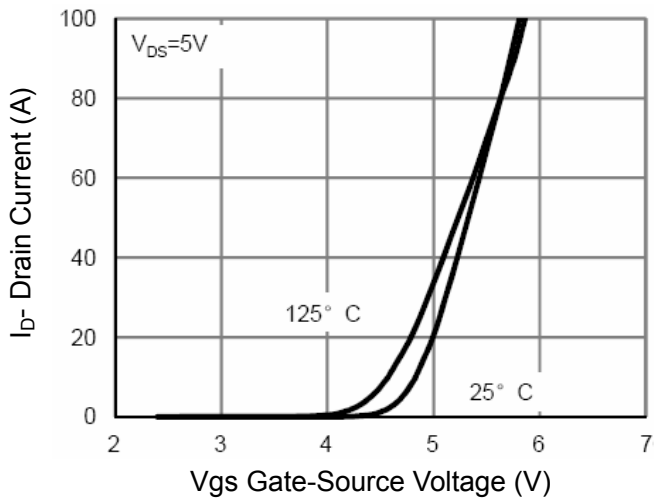
**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition :  $T_J=25^{\circ}C, V_{DD}=40V, V_G=10V, L=0.5mH, R_g=25\Omega$

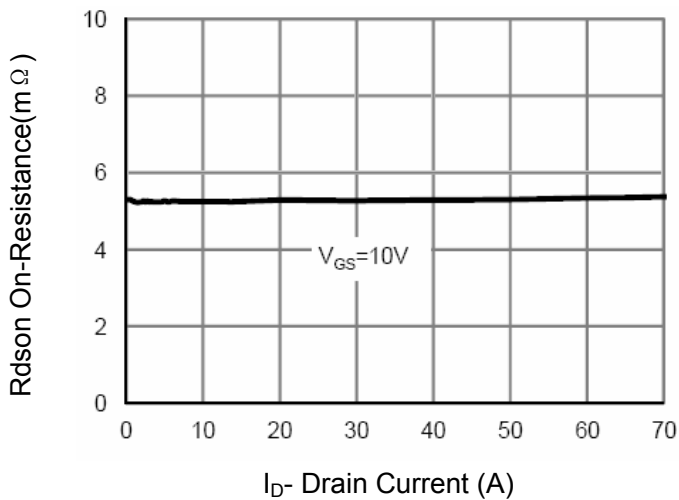
**Typical Electrical and Thermal Characteristics**



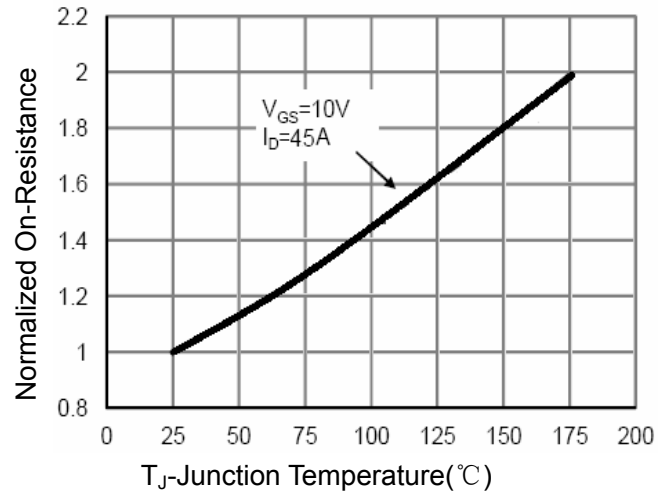
**Figure 1 Output Characteristics**



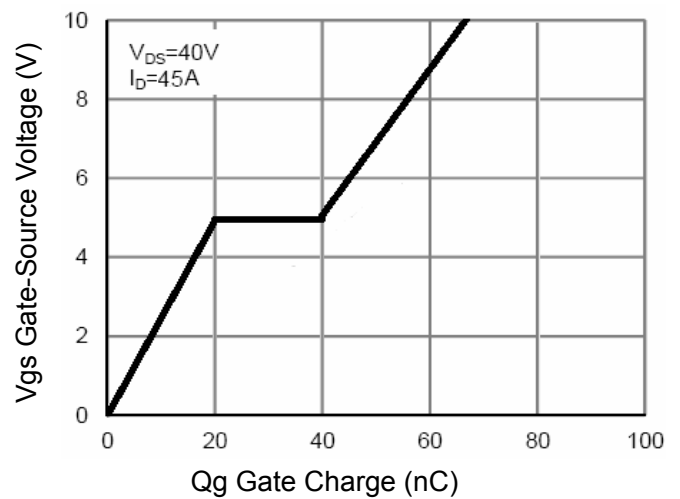
**Figure 2 Transfer Characteristics**



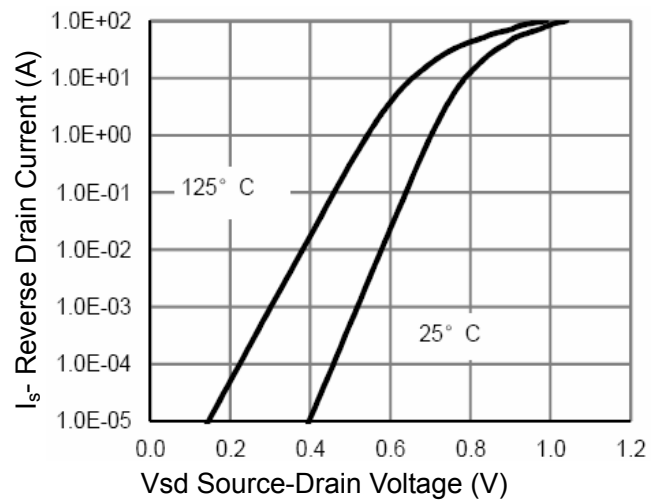
**Figure 3 Rds(on)- Drain Current**



**Figure 4 Rds(on)-Junction Temperature**



**Figure 5 Gate Charge**



**Figure 6 Source- Drain Diode Forward**

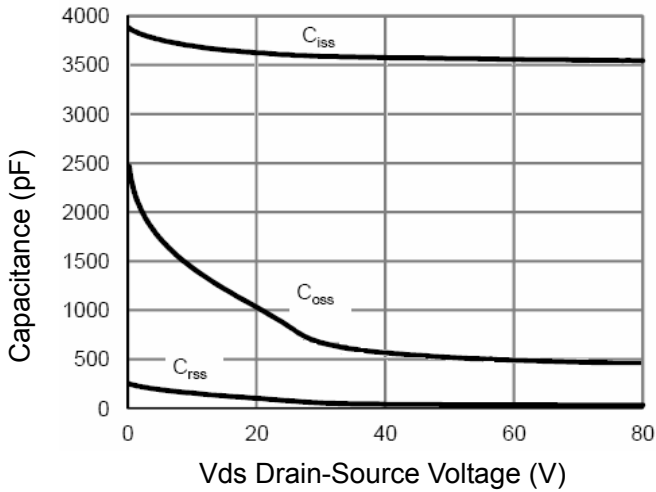


Figure 7 Capacitance vs Vds

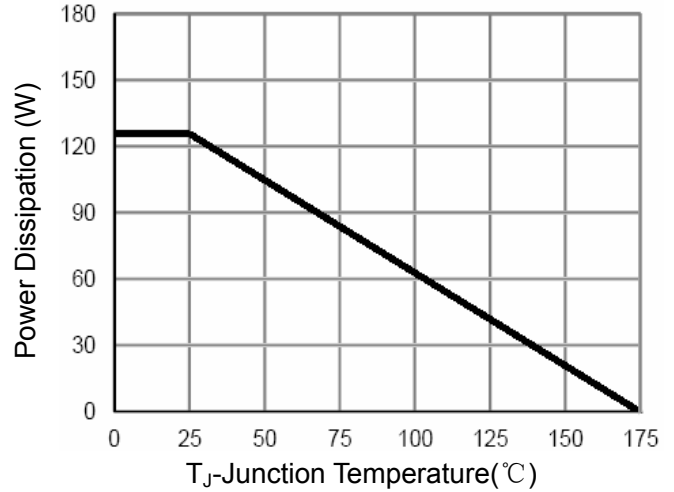


Figure 9 Power De-rating

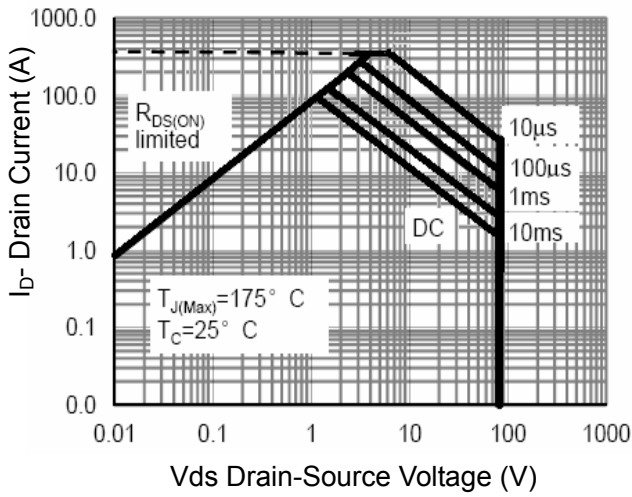


Figure 8 Safe Operation Area

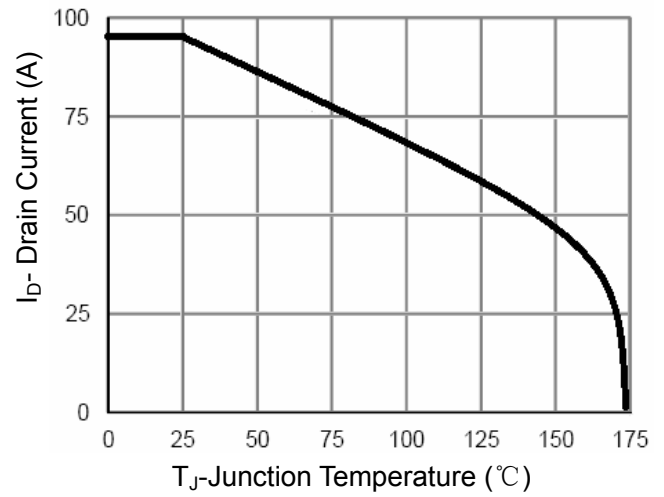


Figure 10 Current De-rating

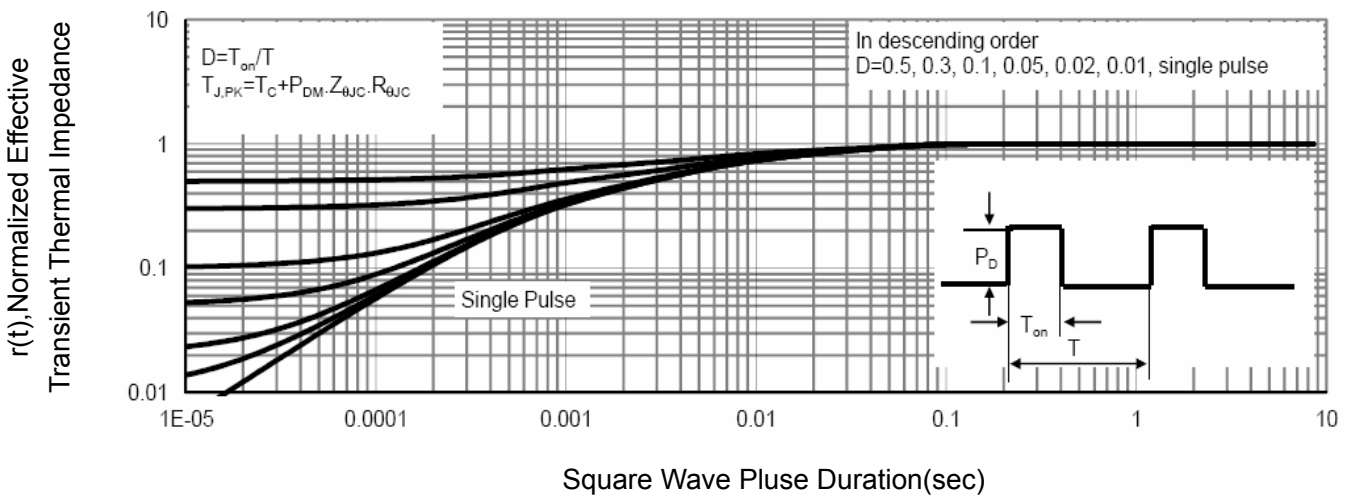
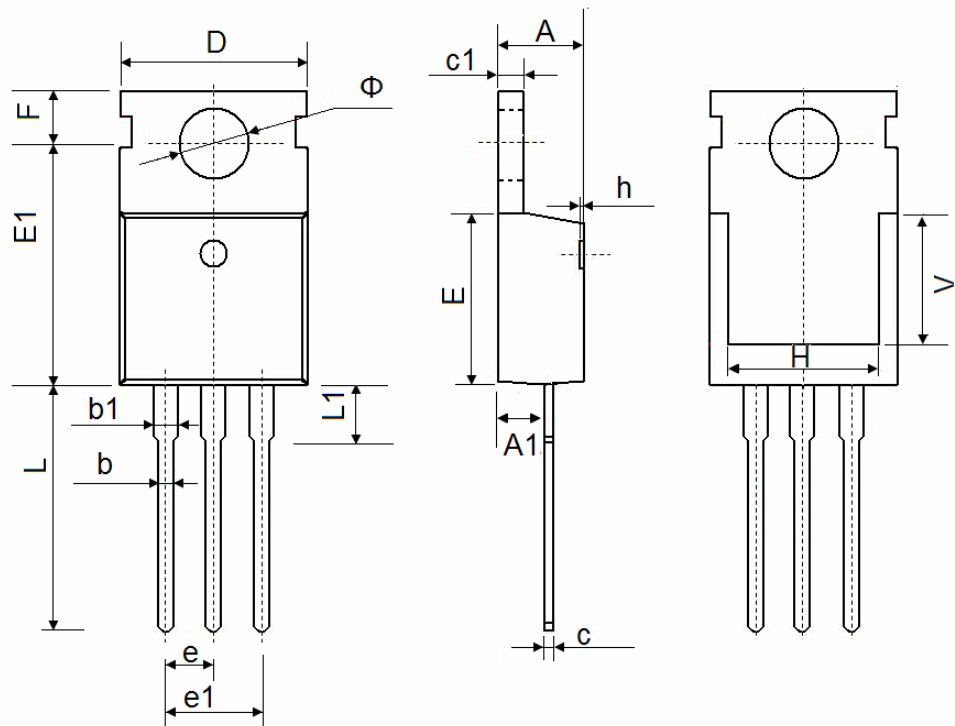
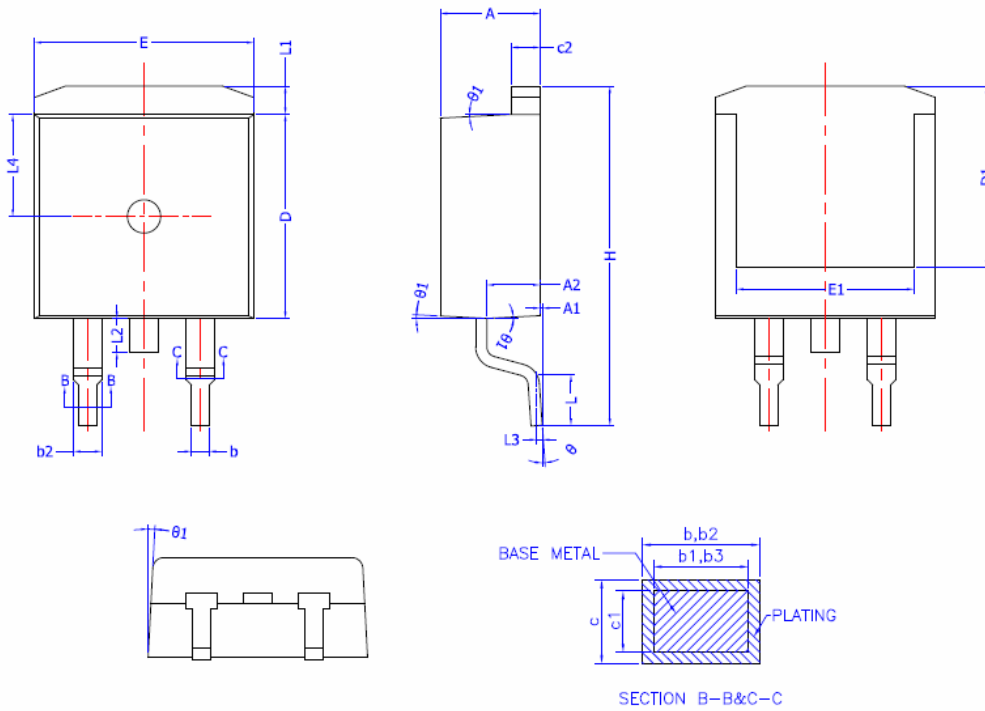


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.9500	9.750	0.352	0.384
E1	12.650	12.950	0.498	0.510
e	2.540 TYP.		0.100 TYP.	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	7.500 REF.		0.295 REF.	
Φ	3.400	3.800	0.134	0.150



COMMON DIMENSIONS  
 (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	0	0.10	0.25
A2	2.20	2.40	2.60
b	0.76	—	0.89
b1	0.75	0.80	0.85
b2	1.23	—	1.37
b3	1.22	1.27	1.32
c	0.47	—	0.60
c1	0.46	0.51	0.56
c2	1.25	1.30	1.35
D	9.10	9.20	9.30
D1	8.00	—	—
E	9.80	9.90	10.00
E1	7.80	—	—
e	2.54 BSC		
H	14.90	15.30	15.70
L	2.00	2.30	2.60
L1	1.17	1.27	1.40
L2	—	—	1.75
L3	0.25BSC		
L4	4.60 REF		
θ	0°	—	8°
θ1	1°	3°	5°